JJMICROELECTRONICS

80V, 33A, 14.5mΩ N-channel Power SGT MOSFET

JMSH08170U2HQ

Features

- Ultra-low ON-resistance, $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested
- 100% ΔVds Tested
- Halogen-free; RoHS-compliant
- AEC-Q101 Qualified

Applications

- Load Switch
- PWM Application
- General Automotive Application

Product Summary

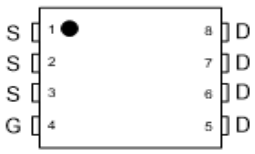
Parameters	Value	Unit
V_{DSS}	80	V
$V_{GS(th)_Typ}$	2.8	V
I_D(@V_{GS}=10V)	33	A
$R_{DS(ON)_Typ}$(@V_{GS}=10V)	14.5	mΩ

RoHS

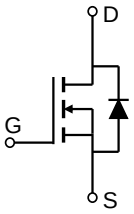




PDFN3X3-8L



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH08170U2HQ-13	SH081702HQ	1	Tape&Reel	PDFN3x3-8L	5000	50000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		80	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	33	A
		T_C = 100°C	23	
I_{DM}	Pulsed Drain Current (1)		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy (2)		74	mJ
P_D	Power Dissipation	T_C = 25°C	43	W
		T_C = 100°C	21	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 175	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.5	

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Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	80	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 64V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.0	2.8	4.0	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 20A	-	14.5	17	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	0.7	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 40V, f = 1MHz	-	625	850	pF
C_{oss}	Output Capacitance		-	127	180	pF
C_{rss}	Reverse Transfer Capacitance		-	12	50	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 40V, I_D = 20A	-	11	-	nC
Q_{gs}	Gate Source Charge		-	4	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 40V I_D= 20A, R_{GEN} = 3Ω	-	7	-	ns
t_r	Turn-On Rise Time		-	16	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	11	-	ns
t_f	Turn-Off Fall Time		-	3	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	33	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	132	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	12	24	35	ns
Qrr	Body Diode Reverse Recovery Charge		-	21	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25C, V_{DD}=40V, V_{GS}=10V, R_G=25ohm, L=3mH, I_{AS}=7A, V_{DD}=0V during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

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Typical Performance Characteristics

Figure 1: Power De-rating

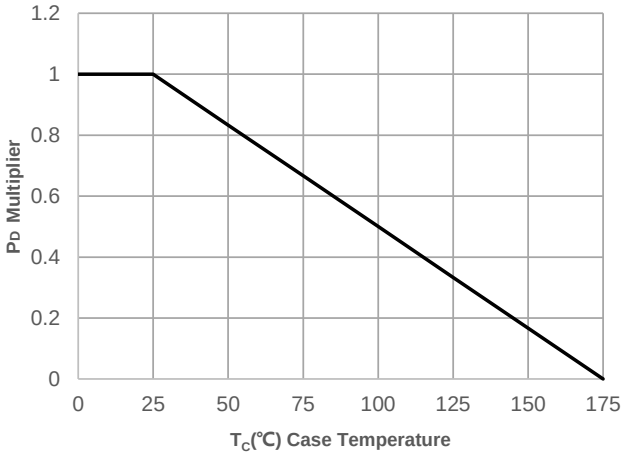


Figure 2: Current De-rating

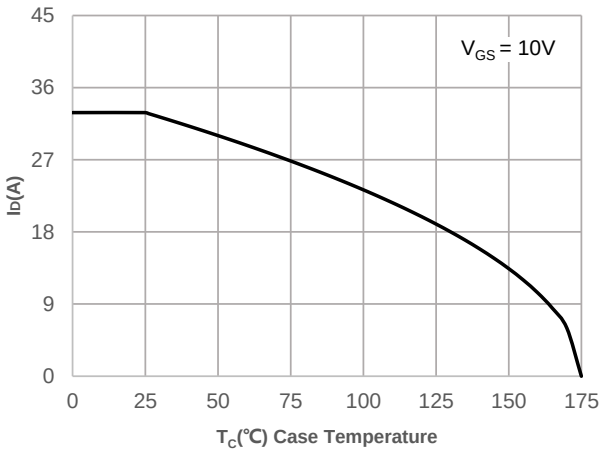


Figure 3: Normalized Maximum Transient Thermal Impedance

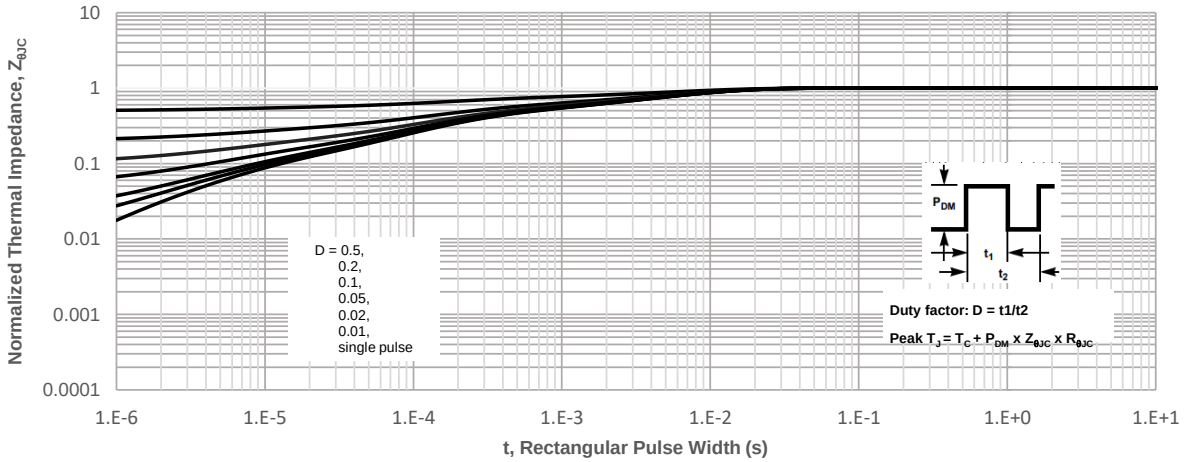
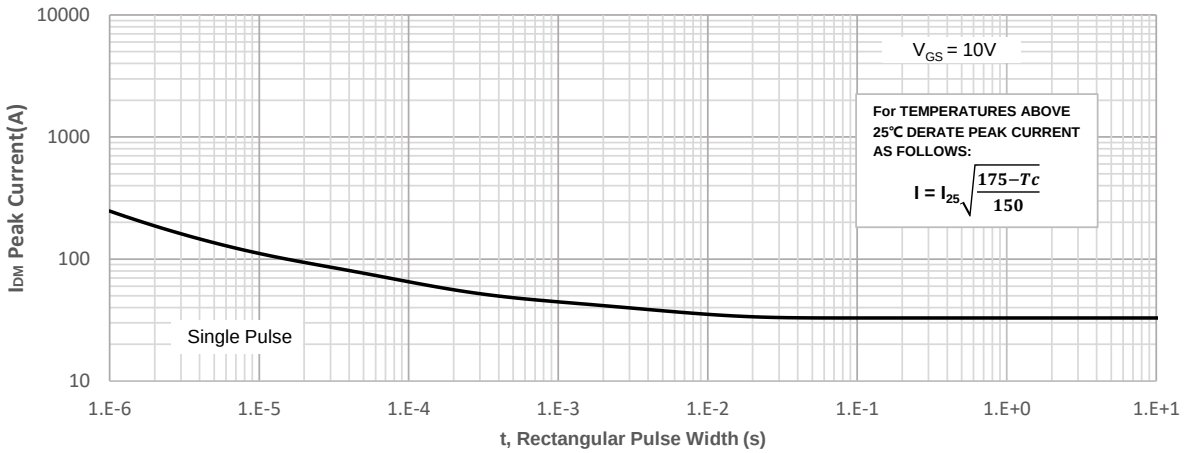


Figure 4: Peak Current Capacity



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Typical Performance Characteristics

Figure 5: Output Characteristics

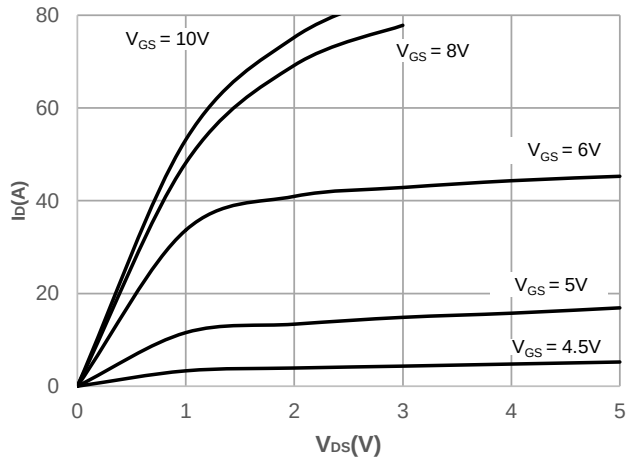


Figure 6: Typical Transfer Characteristics

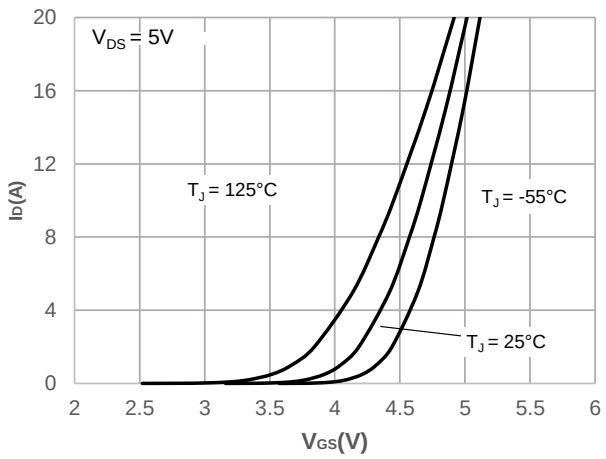


Figure 7: On-resistance vs. Drain Current

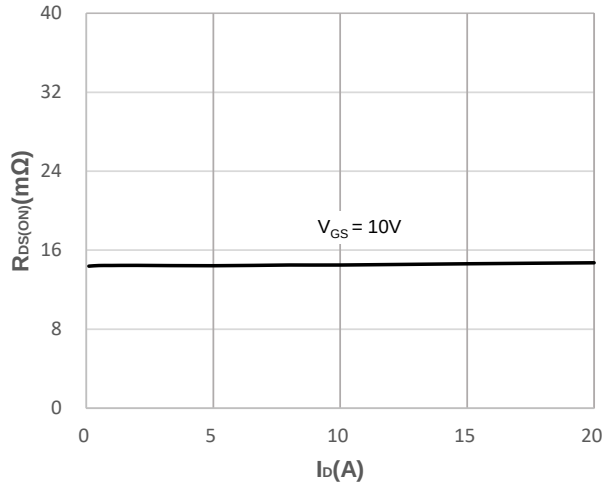


Figure 8: Body Diode Characteristics

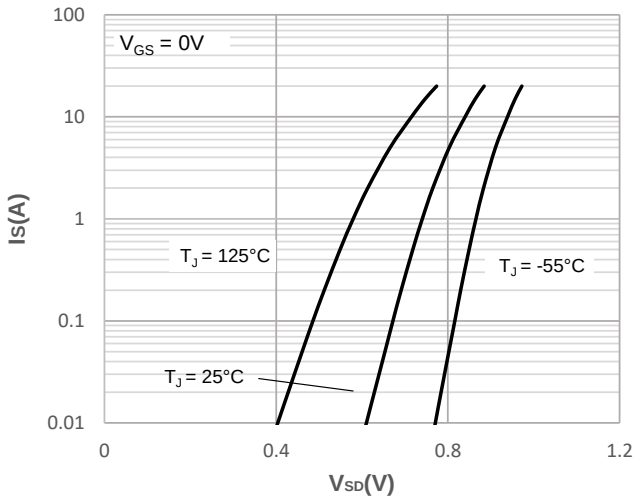


Figure 9: Gate Charge Characteristics

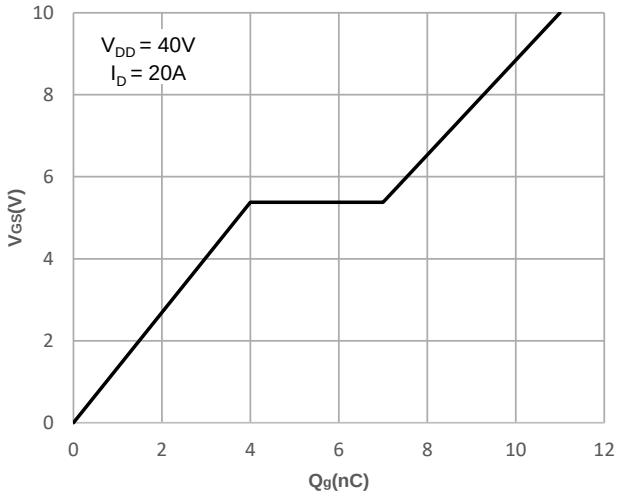
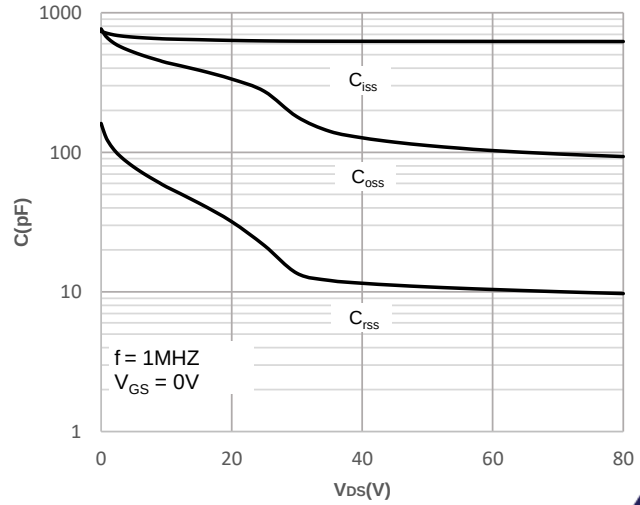


Figure 10: Capacitance Characteristics



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Typical Performance Characteristics

Figure 11: Normalized Breakdown Voltage vs. Junction Temperature

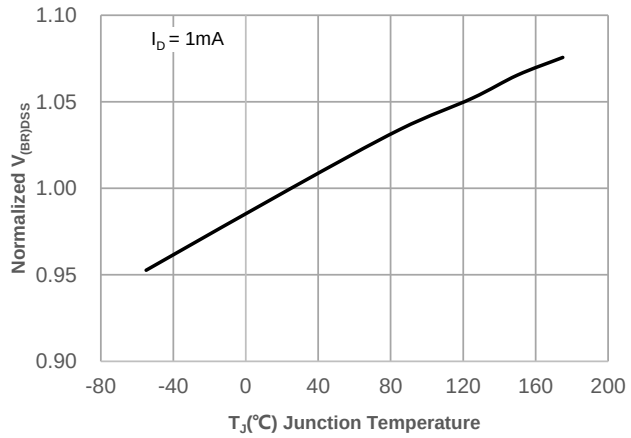


Figure 12: Normalized on Resistance vs. Junction Temperature

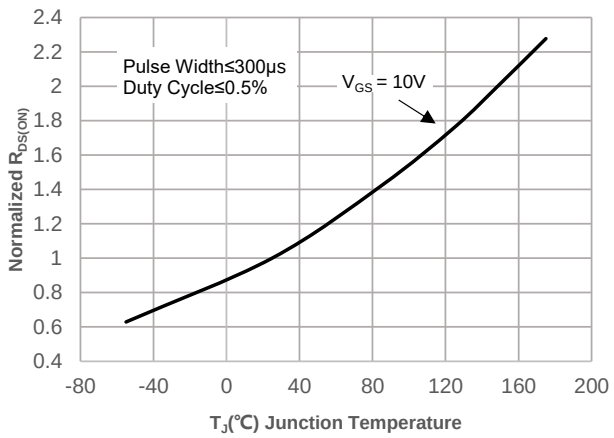


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

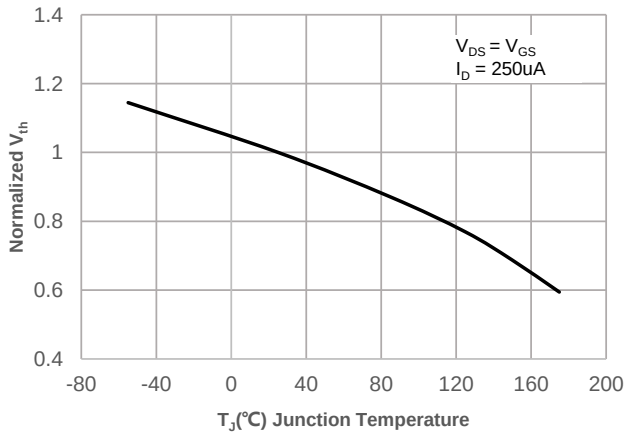


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

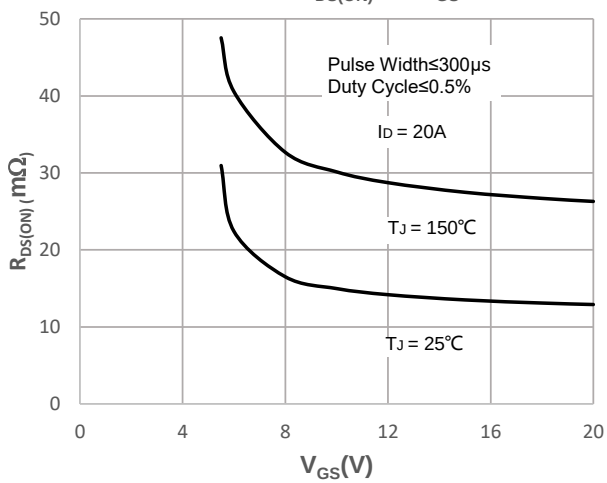
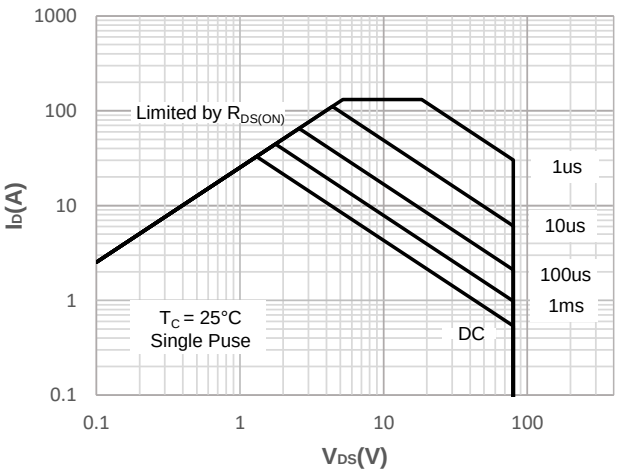


Figure 15: Maximum Safe Operating Area



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Test Circuit

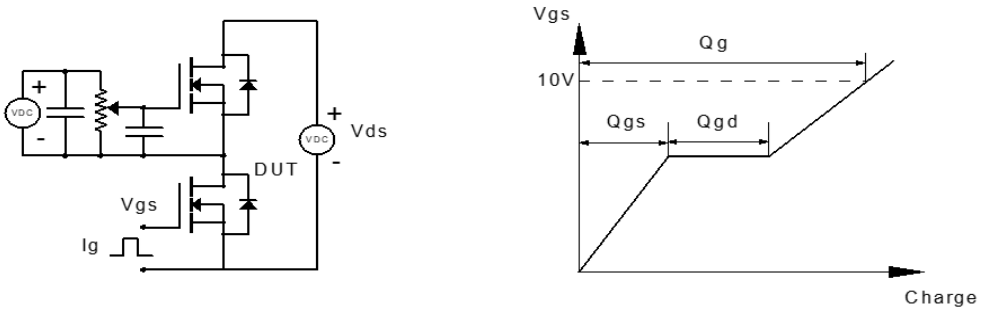


Figure 1: Gate Charge Test Circuit & Waveform

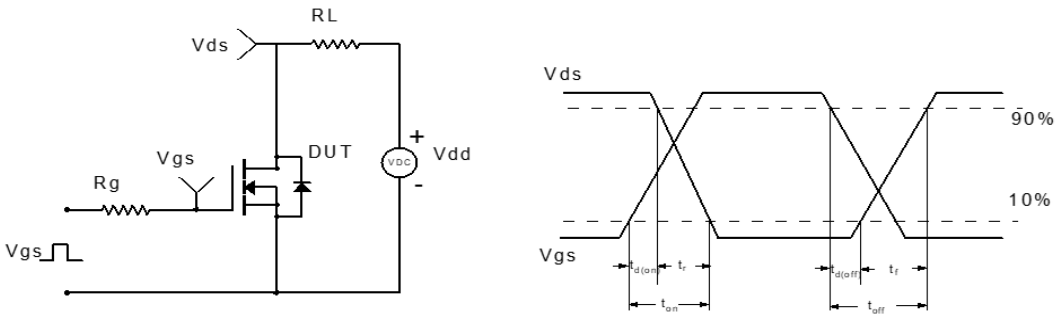


Figure 2: Resistive Switching Test Circuit & Waveform

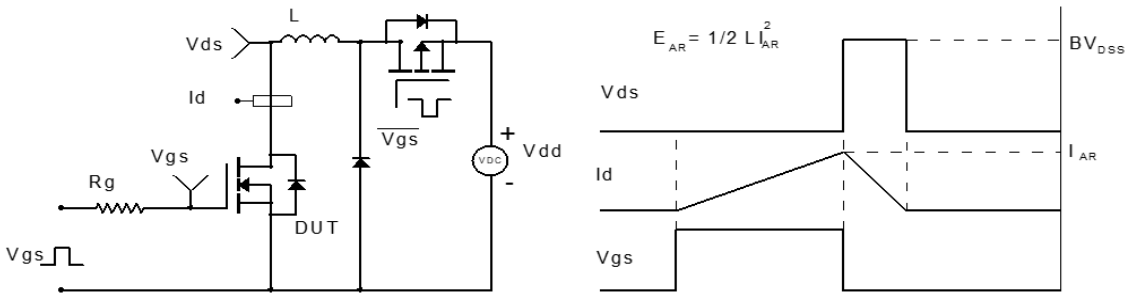


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

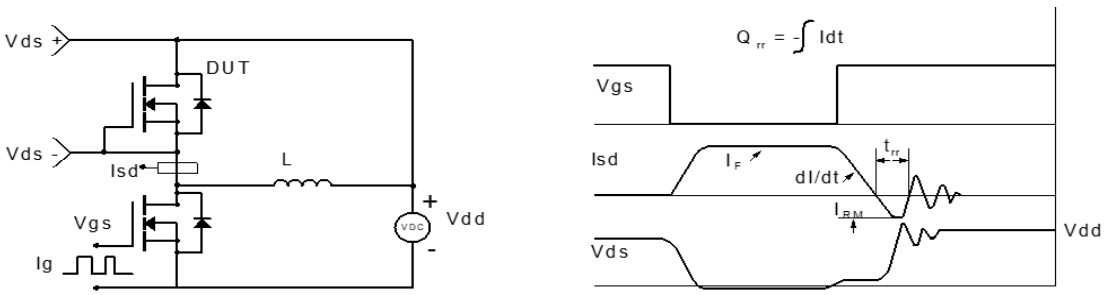
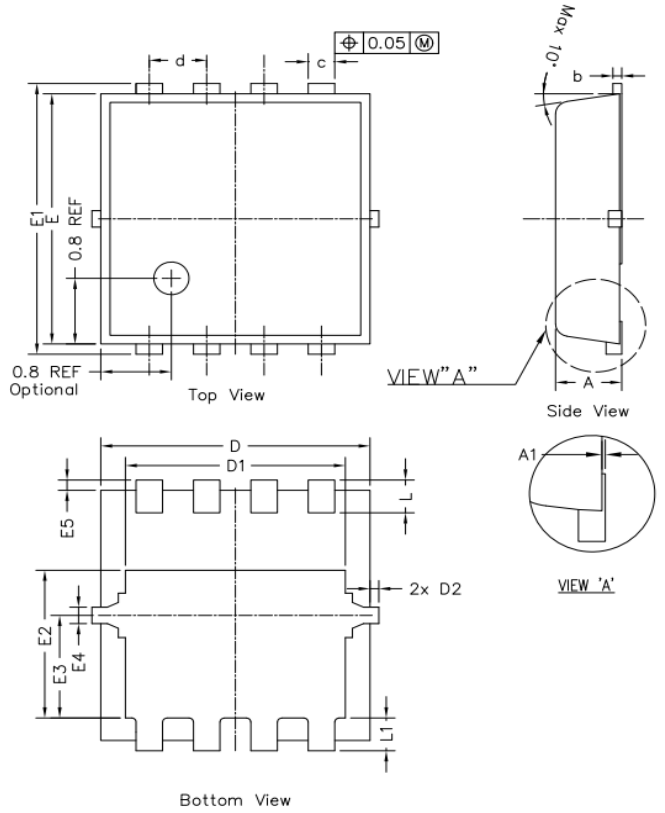


Figure 4: Diode Recovery Test Circuit & Waveform

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Package Mechanical Data(PDFN3X3-8L)



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.031
A1	---	---	0.050	----	----	0.002
b	0.144	0.152	0.202	0.006	0.006	0.008
c	0.250	0.300	0.350	0.010	0.012	0.014
d		0.65 BSC			0.026 BSC	
D	2.950	3.050	3.150	0.116	0.120	0.124
D1	2.390	2.490	2.590	0.094	0.098	0.102
D2	---	---	0.125	---	---	0.005
E	2.950	3.050	3.150	0.116	0.120	0.124
E1	3.200	3.300	3.400	0.126	0.130	0.134
E2	1.700	1.800	1.900	0.067	0.071	0.075
E3	1.150	1.250	1.350	0.045	0.049	0.053
E4	0.150	0.200	0.250	0.006	0.008	0.010
E5	0.075	0.125	0.175	0.003	0.005	0.007
L	0.300	0.400	0.500	0.01	0.02	0.02
L1	0.300	0.400	0.500	0.01	0.02	0.02

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